BAT54AWT1

Preferred Device

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

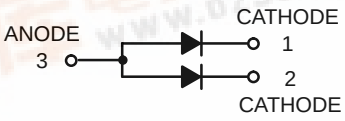
Features

- Extremely Fast Switching Speed
- Low Forward Voltage − 0.35 V (Typ) @ I_F = 10 mAdc
- Pb−Free Package is Available

ON Semiconductor®

http://onsemi.com

30 VOLTS SCHOTTKY BARRIER DETECTOR AND SWITCHING DIODES

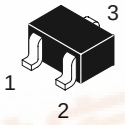


MAXIMUM RATINGS (T_J = 125°C unless otherwise noted)

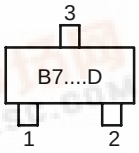
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Power Dissipation @ T_A = 25°C Derate above 25°C	P_F	200 1.6	mW mW/°C
Forward Current (DC)	I_F	200 Max	mA
Junction Temperature	T_J	125 Max	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

MARKING DIAGRAM



SOT−323
CASE 419



B7 = Specific Device Code
D = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BAT54AWT1	SOT−323	3000/Tape & Reel
BAT54AWT1G	SOT−323 (Pb−Free)	3000/Tape & Reel

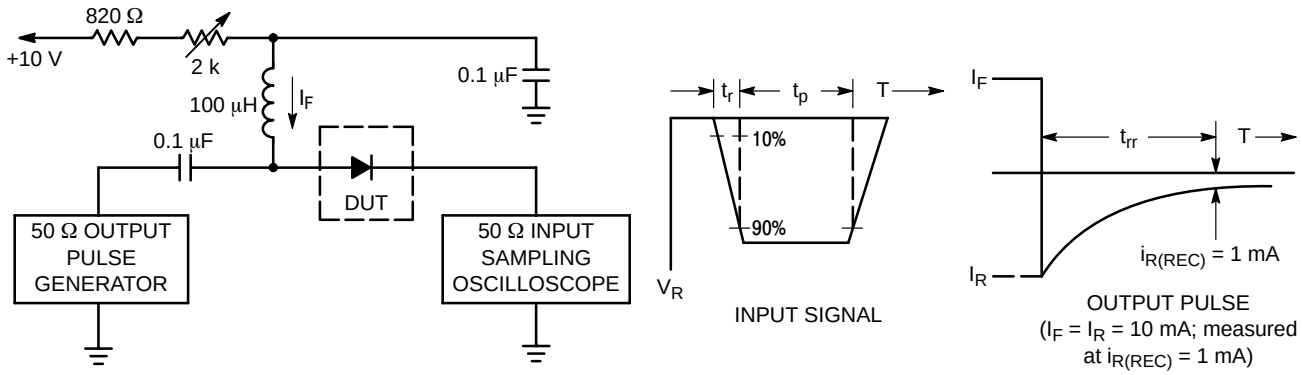
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

Publication Order Number:

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μA)	$V_{(BR)R}$	30	–	–	V
Total Capacitance (V_R = 1.0 V, f = 1.0 MHz)	C_T	–	7.6	10	pF
Reverse Leakage (V_R = 25 V)	I_R	–	0.5	2.0	μAdc
Forward Voltage (I_F = 0.1 mAdc)	V_F	–	0.22	0.24	Vdc
Forward Voltage (I_F = 30 mAdc)	V_F	–	0.41	0.5	Vdc
Forward Voltage (I_F = 100 mAdc)	V_F	–	0.52	0.8	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc, Figure 1)	t_{rr}	–	–	5.0	ns
Forward Voltage (I_F = 1.0 mAdc)	V_F	–	0.29	0.32	Vdc
Forward Voltage (I_F = 10 mAdc)	V_F	–	0.35	0.40	Vdc
Forward Current (DC)	I_F	–	–	200	mAdc
Repetitive Peak Forward Current	I_{FRM}	–	–	300	mAdc
Non−Repetitive Peak Forward Current (t < 1.0 s)	I_{FSM}	–	–	600	mAdc



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

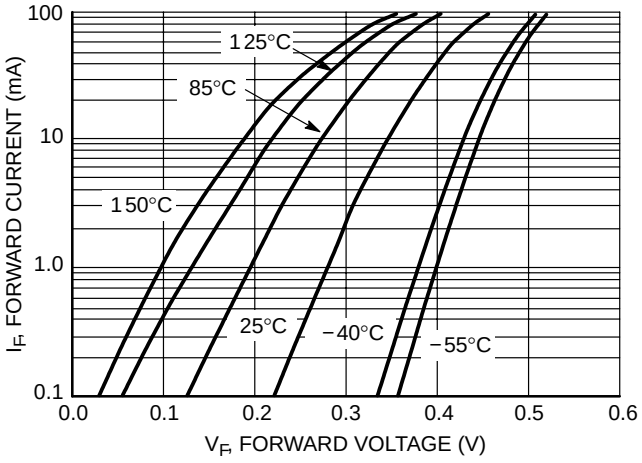


Figure 2. Forward Voltage

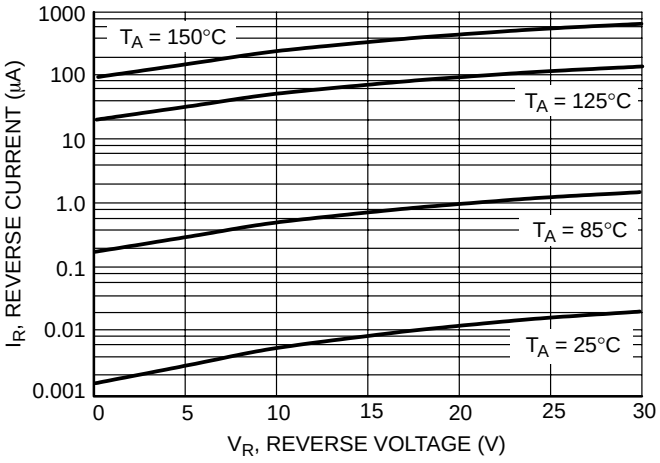


Figure 3. Leakage Current

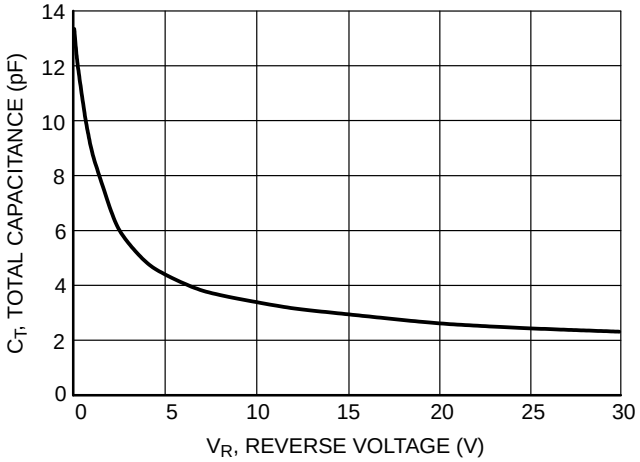
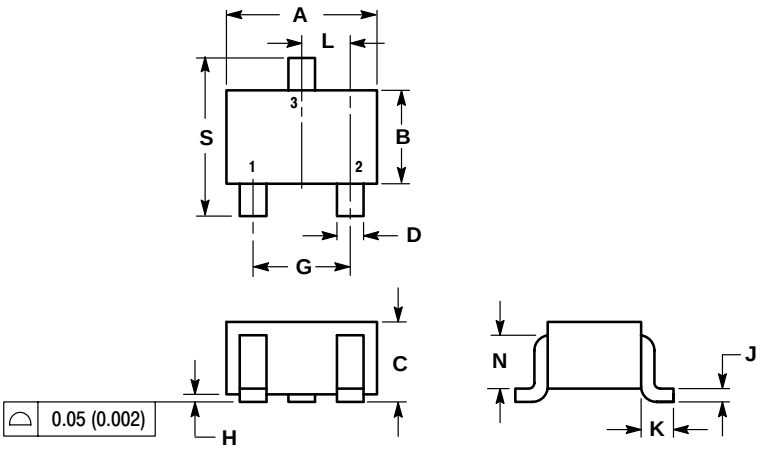


Figure 4. Total Capacitance

BAT54AWT1

PACKAGE DIMENSIONS

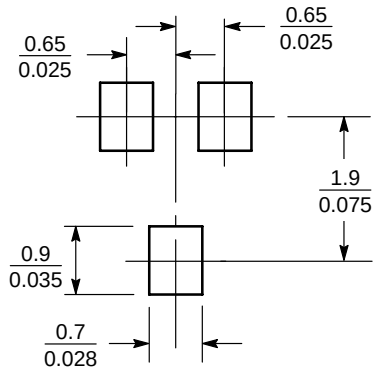
SOT−323 (SC−70)
CASE 419−04
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
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Email: orderlit@onsemi.com

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Japan: ON Semiconductor, Japan Customer Focus Center
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Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

BAT54AWT1/D